

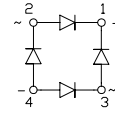
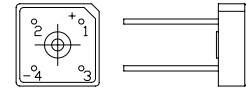
# DIODE Type: PB10S1,2,4,6

## OUTLINE DRAWING

SINGLE – PHASE SILICON BRIDGE RECTIFIER

### FEATURES

- \* Surge Overload Rating : 150 Amperes Peak
- \* Low Forward Voltage Drop
- \* Mounting Position : Any



### Maximum Ratings

Approx Net Weight:8.5g

Rating	Symbol	PB10S1	PB10S2	PB10S4	PB10S6	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	100	200	400	600	V
Non-repetitive Peak Reverse Voltage	$V_{RSM}$	120	240	480	680	V
Average Rectified Output Current	$I_O$	10	Tc=102°C, With 200x200x1.5mm,Al-Fin Ta=40°C, Without Fin			A
		3.7				
Surge Forward Current Per 1 Arm	$I_{FSM}$	150	50 Hz Half Sine Wave,1cycle Non-repetitive			A
Operating Junction Temperature Range	$T_{jw}$	- 40 to + 150				°C
Storage Temperature Range	$T_{stg}$	- 40 to + 150				°C
Insulation Withstand Voltage	$V_{iso}$	1500	Terminal to Base, AC 1min.			V
Mounting torque	$F_w$	0.5	Recommended value			N.m

### Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current Per 1 Arm	$I_{RM}$	Tj= 25°C, $V_{RM}= V_{RRM}$	-	-	5	μA
Peak Forward Voltage Per 1 Arm	$V_{FM}$	Tj= 25°C, $I_{FM}= 5A$	-	-	1.0	V
Thermal Resistance	$R_{th(j-c)}$	Junction to Case(total)	-	-	3.5	°C/W

PB10S1,2,4,6 OUTLINE DRAWING (Dimensions in mm)

